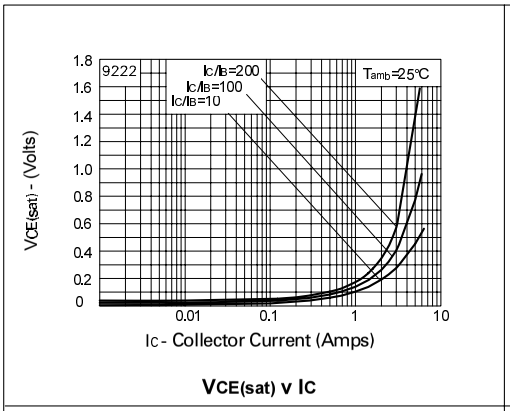
THE DATASHEET OF

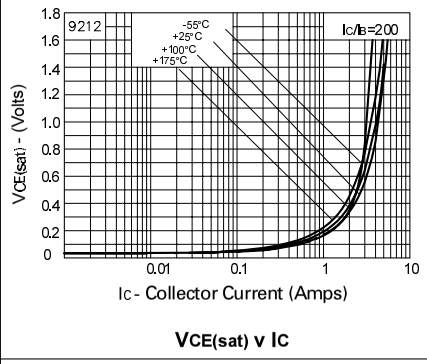
FZT788ATA

FZT788B

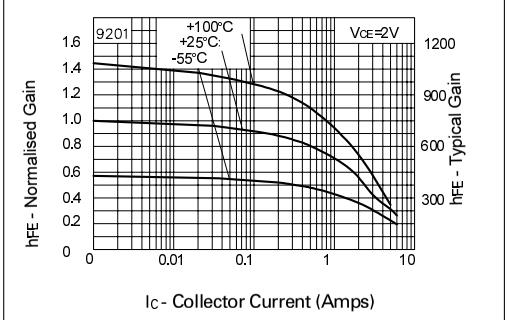
TYPICAL CHARACTERISTICS



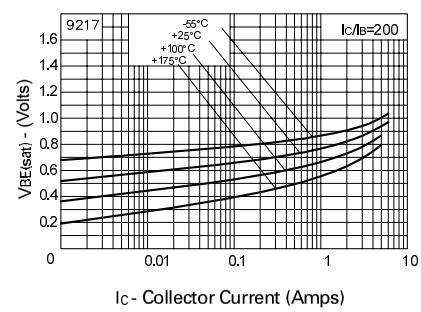
VCE(sat) v IC



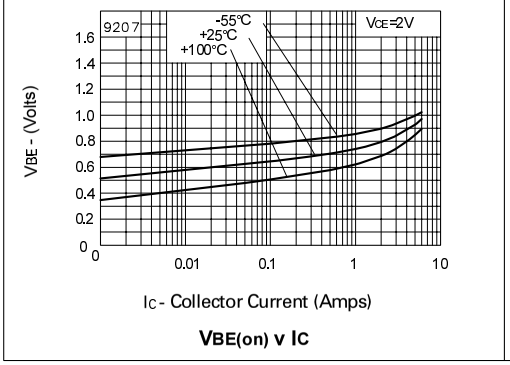
VCE(sat) v IC



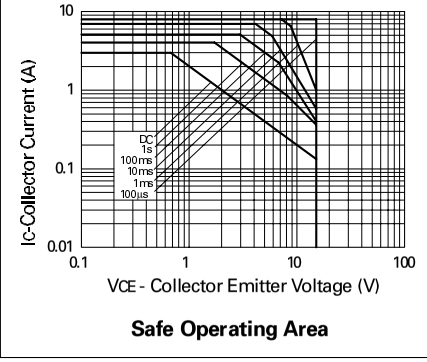
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area

SOT223 PNP SILICON PLA
POWER HIGH GAIN TRANS

ISSUE 3 - OCTOBER 1995

FEATURES

* Low equivalent on-resistance; $R_{CE(sa}$
* Gain of 300 at I_C=2 Amps and Very l

APPLICATIONS

* Battery powered circuits

COMPLEMENTAY TYPE – FZT688B

PARTMARKING DETAIL – FZT788B

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Peak Pulse Current
Continuous Collector Current
Power Dissipation at T_{amb}=25°C
Operating and Storage Temperature Ran

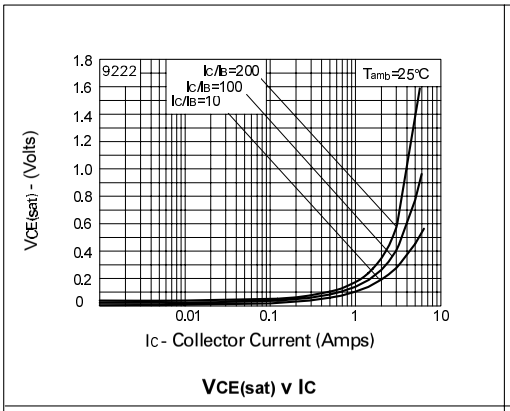
ELECTRICAL CHARACTERISTICS

PARAMETER	SYMI
Collector-Base Breakdown Voltage	$V_{(BR)C}$
Collector-Emitter Breakdown Voltage	$V_{(BR)C}$
Emitter-Base Breakdown Voltage	$V_{(BR)E}$
Collector Cut-Off Current	I_{CBO}
Emitter Cut-Off Current	I_{EBO}
Collector-Emitter Saturation Voltage	$V_{CE(sa}$
Base-Emitter Saturation Voltage	$V_{BE(sa}$
Base-Emitter Turn-On Voltage	$V_{BE(o}$
Static Forward Current Transfer Ratio	h_{FE}
Transition Frequency	f_T
Input Capacitance	C_{ibo}
Output Capacitance	C_{obo}
Switching Times	t_{on} t_{off}

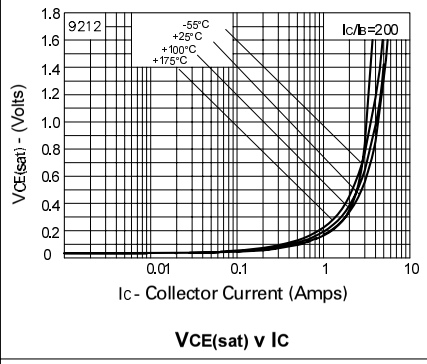
*Measured under pulsed conditions. Pulse
Spice parameter data is available upon rec

FZT788B

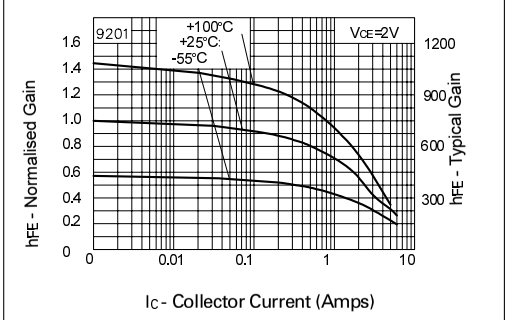
TYPICAL CHARACTERISTICS



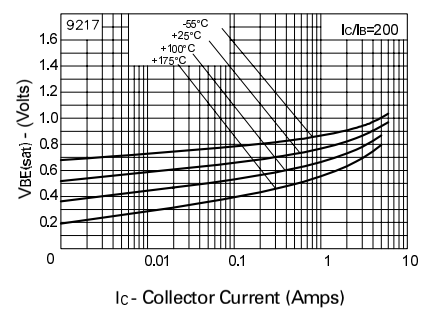
VCE(sat) v IC



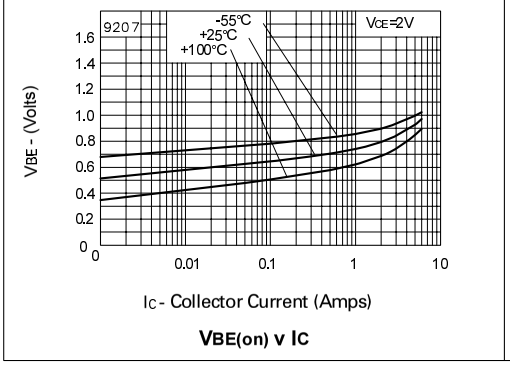
VCE(sat) v IC



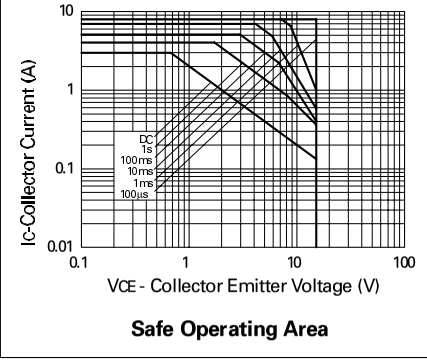
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area

SOT223 PNP SILICON PLA
POWER HIGH GAIN TRANS

ISSUE 3 - OCTOBER 1995

FEATURES

* Low equivalent on-resistance; $R_{CE(sa}$
* Gain of 300 at I_C=2 Amps and Very l

APPLICATIONS

* Battery powered circuits

COMPLEMENTAY TYPE – FZT688B

PARTMARKING DETAIL – FZT788B

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Peak Pulse Current
Continuous Collector Current
Power Dissipation at T_{amb}=25°C
Operating and Storage Temperature Ran

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMI
Collector-Base Breakdown Voltage	$V_{(BR)C}$
Collector-Emitter Breakdown Voltage	$V_{(BR)C}$
Emitter-Base Breakdown Voltage	$V_{(BR)E}$
Collector Cut-Off Current	I_{CBO}
Emitter Cut-Off Current	I_{EBO}
Collector-Emitter Saturation Voltage	$V_{CE(sa}$
Base-Emitter Saturation Voltage	$V_{BE(sa}$
Base-Emitter Turn-On Voltage	$V_{BE(o}$
Static Forward Current Transfer Ratio	h_{FE}
Transition Frequency	f_T
Input Capacitance	C_{ibo}
Output Capacitance	C_{obo}
Switching Times	t_{on} t_{off}

*Measured under pulsed conditions. Pulse
Spice parameter data is available upon rec

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

- View FZT788ATA on WIN SOURCE
- Diodes Incorporated Information

Optimize Your Supply Chain with WIN SOURCE Solutions

- Global Sourcing Solution
- Obsolete Management
- Cost Control Management
- Shortage Management
- Alternative Solution
- Excess Inventory Management